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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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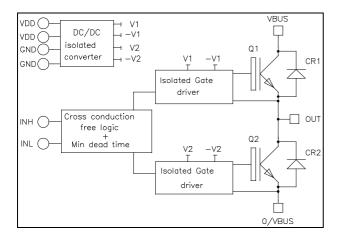






Phase leg Intelligent Power Module





Application

- Motor control
- Uninterruptible Power Supplies
- Switched Mode Power Supplies
- Amplifier

Features

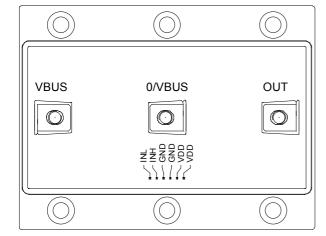
- Non Punch Through (NPT) FAST IGBT
 - Low voltage drop
 - Low tail current
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA & SCSOA rated

• Integrated Fail Safe IGBT Protection (Driver)

- Top Bottom input signals Interlock
- Isolated DC/DC Converter
- Low stray inductance
- M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Very high noise immunity (common mode rejection > 25kV/μs)
- Galvanic Isolation: 3750V for the optocoupler 2500V for the transformer
- 5V logic level with Schmitt-trigger Input
- Single V_{DD}=5V supply required
- Secondary auxiliary power supplies internally generated (15V, -6V)
- Optocoupler qualified to AEC-Q100 test guidelines
- · RoHS compliant



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

1. Inverter Power Module

Absolute maximum ratings

| Symbol | Parameter | | Max ratings | Unit |
|-------------|---------------------------------------|------------------------|--------------|------|
| V_{CES} | Collector - Emitter Breakdown Voltage | | 1200 | V |
| $I_{\rm C}$ | Continuous Collector Current | $T_C = 25$ °C | 400 | |
| | Continuous Conector Current | $T_C = 80$ °C | 300 | Α |
| I_{CM} | Pulsed Collector Current | $T_C = 25$ °C | 600 | |
| P_{D} | Maximum Power Dissipation | $T_C = 25$ °C | 1780 | W |
| RBSOA | Reverse Bias Safe Operating Area | $T_{j} = 125^{\circ}C$ | 600A @ 1200V | |

Electrical Characteristics

| | Symbol | Characteristic | Test Conditions | | Min | Typ | Max | Unit |
|------------------|----------------------|--------------------------------------|--------------------------------|------------------------|-----|-----|-----|------|
| | T | Zero Gate Voltage Collector Current | $V_{GE} = 0V$ | $T_j = 25$ °C | | | 500 | μA |
| I _{CES} | ICES | Zero Gate Voltage Concetor Current | $V_{CE} = 1200V$ | $T_j = 125$ °C | | | 750 | μД |
| | V | Collector Emitter Saturation Voltage | $V_{\rm DD} = V_{\rm IN} = 5V$ | $T_j = 25$ °C | | 3.2 | 3.9 | 17 |
| | V _{CE(sat)} | Conector Emitter Saturation Voltage | $I_{\rm C} = 300 A$ | $T_{i} = 125^{\circ}C$ | | 4 | | · |

Dynamic Characteristics

| Symbol | Characteristic | Test Conditions | Min | Тур | Max | Unit |
|------------------|-------------------------------------|--|-----|------|------|--------------|
| Cies | Input Capacitance | $V_{GE} = 0V$ | | 21 | | |
| C_{oes} | Output Capacitance | $V_{CE} = 25V$ | | 2.9 | | nF |
| C_{res} | Reverse Transfer Capacitance | f = 1MHz | | 1.52 | | |
| $T_{\rm r}$ | Rise Time | Inductive Switching (25°C) | | 50 | | 12 .0 |
| T_{f} | Fall Time | $V_{DD} = V_{IN} = 5V$ $V_{Bus} = 600V ; I_C = 300A$ | | 30 | | ns |
| $T_{\rm r}$ | Rise Time | Inductive Switching (125°C) | | 60 | | *** |
| $T_{\rm f}$ | Fall Time | $V_{DD} = V_{IN} = 5V$ $V_{Bus} = 600V$ $I_C = 300A$ | | 40 | | ns |
| Eon | Turn-on Switching Energy | | | 25 | | Т |
| E_{off} | Turn-off Switching Energy | | | 15 | | mJ |
| I_{sc} | Short Circuit data | $V_{DD} = V_{IN} = 5V; V_{Bus} = 900V$ $t_p \le 10 \mu s; T_j = 125 ^{\circ} C$ | | 1800 | | A |
| R_{thJC} | Junction to Case thermal resistance | | | | 0.07 | °C/W |



Reverse diode ratings and characteristics

| Symbol | Characteristic | Test Conditions | | Min | Typ | Max | Unit |
|------------------|---|---|---|------|-----|------------|------|
| V_{RRM} | Maximum Peak Repetitive Reverse Voltage | | | 1200 | | | V |
| I_{RM} | Maximum Reverse Leakage Current | V _R =1200V | $T_i = 25$ °C $T_i = 125$ °C | | | 250 500 | μΑ |
| I_{F} | DC Forward Current | | $T_i = 123 \text{ C}$ $T_c = 80^{\circ}\text{C}$ | | 300 | 300 | A |
| $V_{\rm F}$ | Diode Forward Voltage | $I_F = 300A$ | $T_i = 25^{\circ}C$ | | 2.1 | | V |
| V _F | | | $T_{i} = 125^{\circ}C$ | | 1.9 | | V |
| t _{rr} | Reverse Recovery Time | | $T_j = 25$ °C | | 120 | | ns |
| ·rr | | | $T_j = 125$ °C | | 210 | | 115 |
| Q _{rr} | Reverse Recovery Charge | $I_F = 300A$ $V_R = 600V$ $di/dt = 6000A/\mu s$ | $T_j = 25$ °C | | 22 | | μС |
| Qrr | Reverse Recovery Charge | | $T_{i} = 125^{\circ}C$ | | 56 | | μС |
| Б | Daviana Dagayany Engagy | | $T_j = 25$ °C | | 7.2 | | m I |
| E _{rr} | Reverse Recovery Energy | | $T_{j} = 125^{\circ}C$ | | 18 | | mJ |
| R_{thJC} | Junction to Case Thermal Resistance | | | | | 0.12 | °C/W |

2. Driver

Absolute maximum ratings

| Symbol | 1 | Parameter | Max ratings | Unit |
|-----------------------|-----------------------------|--|-------------|------|
| $V_{ m DD}$ | Supply Voltage | | 5.5 | V |
| V_{INi} | Input signal voltage i=L, H | | 5.5 | · |
| I_{VDDmax} | Maximum Supply current | $V_{INi} = 0V$, $i = L \& H$ | 0.35 | |
| | | $V_{DD} = 5V, V_{INH} = /V_{INL}; F_{out} = 50 \text{kHz}$ | 2 | Α |
| f_{max} | Maximum Switching Frequence | cy | 50 | kHz |

Driver Electrical Characteristics

| Symbol | Characteristic | Test Conditions | Min | Typ | Max | Unit |
|------------------------|---|----------------------------|------|-------|-----|-----------|
| $V_{ m DD}$ | Operating Supply Voltage | | 4.5 | 5 | 5.5 | V |
| V _{INi(max)} | Maximum Input Voltage | | -0.5 | 5 | 5.5 | |
| V _{INi (th+)} | Positive Going Threshold Voltage | i = L, H | | 3.2 | | V |
| V _{INi(th-)} | Negative Going Threshold Voltage | , i. L, ii | | 1 | | |
| R_{INi} | Input Resistance * | Ī | | 1 | | kΩ |
| $T_{d(on)}$ | Turn On delay time | Driver + IGBT | | 1100° | | |
| D_T | Built in dead time | | | 600 | | ns |
| $T_{d(off)}$ | Turn Off delay time | Driver + IGBT | | 750 | | |
| PWD | Pulse Width Distortion | | | | 300 | |
| PDD | Propagation Delay Difference between any two driver | $T_{d(on)}$ - $T_{d(off)}$ | -350 | | 350 | ns |
| V_{ISOL} | Primary to Secondary Isolation | | 2500 | | | V_{RMS} |

^{*} Low impedance guarantees good noise immunity.

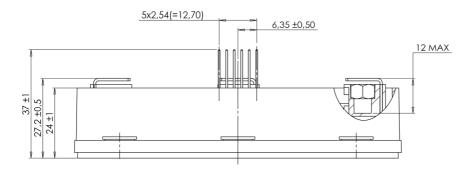
[•] Including built in dead time.

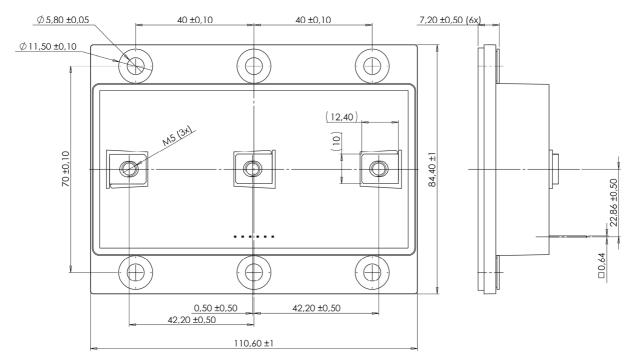


3. Package characteristics

| Symbol | Characteristic | | | Min | Typ | Max | Unit |
|-----------------|--|-------------|----|------|-----|--------|------|
| V_{ISOL} | RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz | | | 4000 | | | V |
| $T_{\rm J}$ | Operating junction temperature range Operating Ambient Temperature | | | -40 | | 150 | |
| T _{OP} | | | | -40 | | 85 | °C |
| T_{STG} | Storage Temperature Range | | | -40 | | 100 | |
| $T_{\rm C}$ | Operating Case Temperature | | | -40 | | 100 | |
| Torque | Mounting forgue | To heatsink | M5 | 2 | | 4.7 | N.m |
| Torque | | M5 | 2 | | 4 | 11.111 | |
| Wt | Package Weight | | | | 550 | | g |

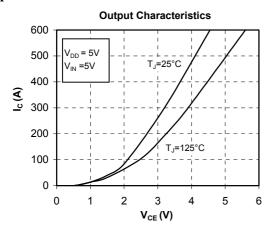
4. LP8 Package outline (dimensions in mm)

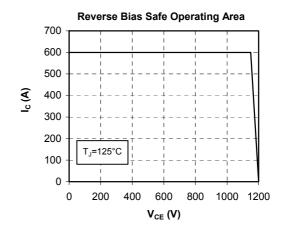


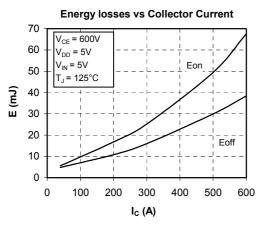


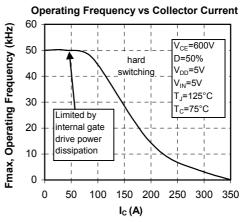


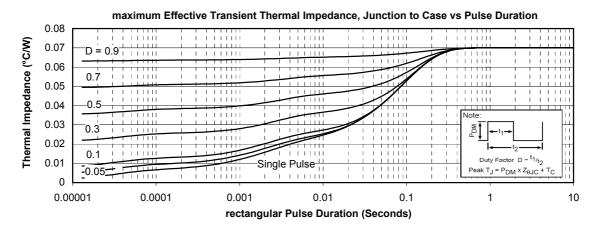
Typical IGBT Performance Curve





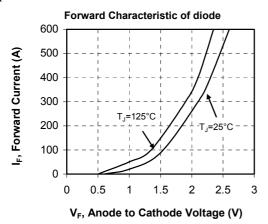


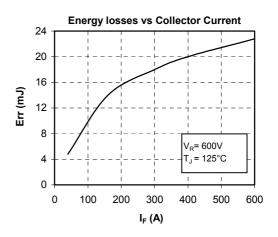




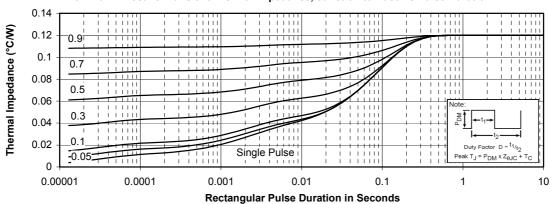


Typical diode Performance Curve





maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration





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